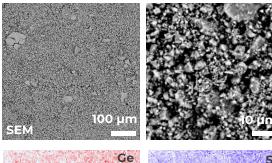
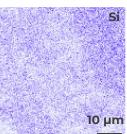
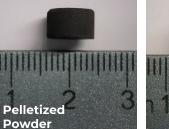


#### Typical Morphology and EDS Maps of Mechanically Alloyed Ge-Si





Elemental 10 µm EDS Maps





\*SEM (BSD) Image corresponding to Elemental EDS Maps

## MATERIAL INFORMATION

# MATERIAL DATA SHEET

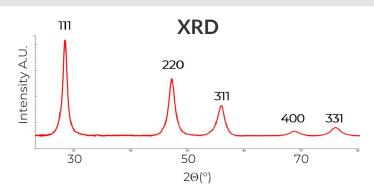
## SERIES S: SEMI-CONDUCTING POWDER

### Si40Ge (40% Germanium Silicon Alloy Powder)

Due to its high mechanical strength, ability to operate at high temperature while maintaining electronic stability, as well as a high resistance to oxidation, Silicon-Germanium has been the material of choice in thermoelectric devices being deployed in the most extreme environments.

This material's unique properties in transistor applications show improved performance in low-current and high-frequency regimes with compositionally and structurally tunable band-gap energies. Work with this material has demonstrated practicality in additive manufacturing with great potential to scale based on customer needs.

This mechanically alloyed powder material is available in bulk, and may be manufactured into parts via powder metal-based processes, such as spark plasma sintering. Compositional analogs available upon request.



TEST	RESULTS**	NOTES
Tap Density	0.834 g/ml	
Specific Gravity (Pycnometer)	3.0190 ± 0.0401 g/cm <sup>3</sup>	
Powder Size (PSA)	Dı₀ [μm] 0.7200 D₅₀ [μm] 3.243 D9₀ [μm] 33.88	Mean size [µm] 11.658 Span 10.220 D [5,3] [µm] 22.627 Fit error 0.0219
Surface Area (BET)	6.26557 m²/g	
Crystal Structure	Mechanically alloyed Si/Ge crystal structure indexed to SG227	No elemental Ge or Si is present in the pattern

\*\*Actual results may vary